

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-20V	5.5mΩ @ V _{GS} = -4.5V	-40A
	7.5mΩ @ V _{GS} = -2.5V	-40A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

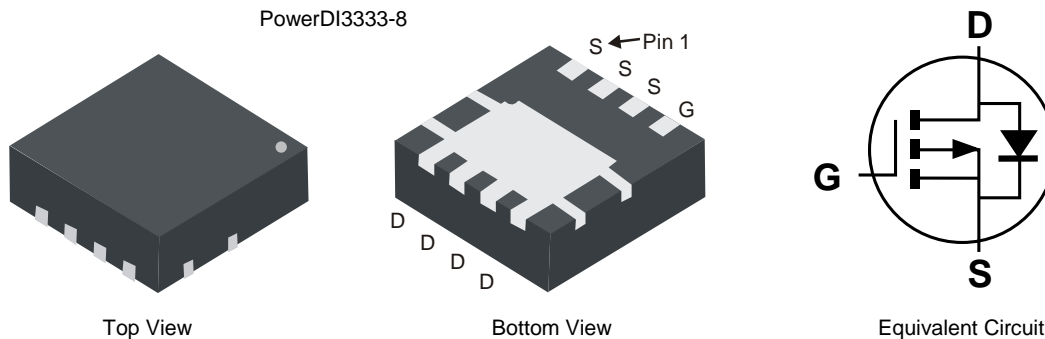
- Load Switch
- Power Management Functions

Features

- Low R_{DS(ON)} – Ensures On State Losses are Minimized
- Small Form Factor, Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.030 grams (Approximate)

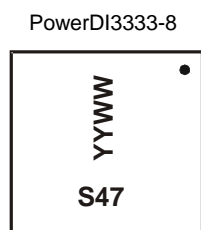


Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2006UFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP2006UFGQ-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



S47 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±10	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	T _A = +25°C	-17.5
Steady State		T _A = +70°C	-14.0
		T _C = +25°C	-40
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-2.2	A
Avalanche Current (Note 8) L = 0.1mH	I _{AS}	-23	A
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	28	mJ

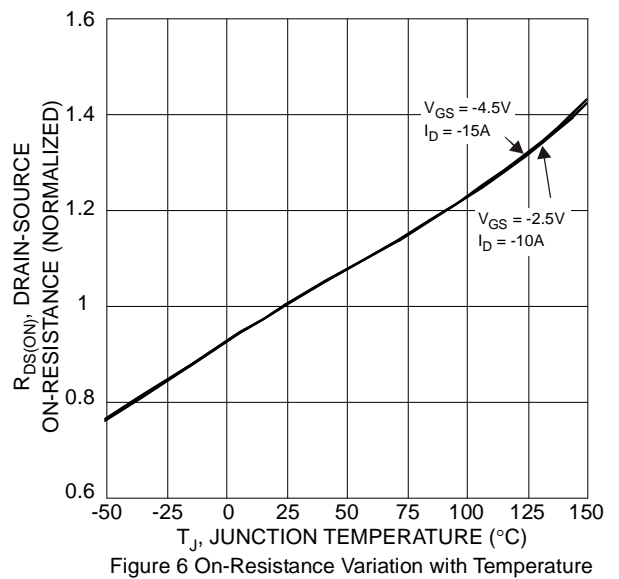
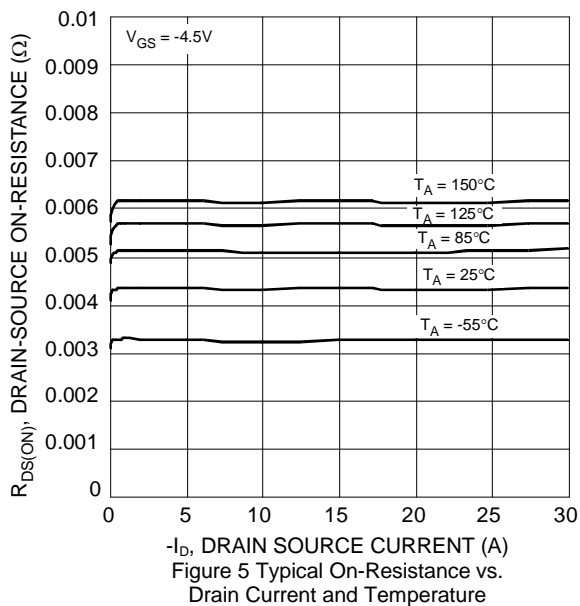
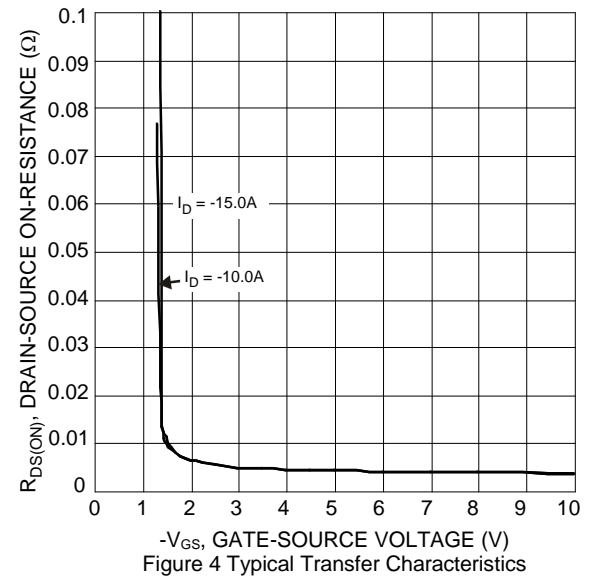
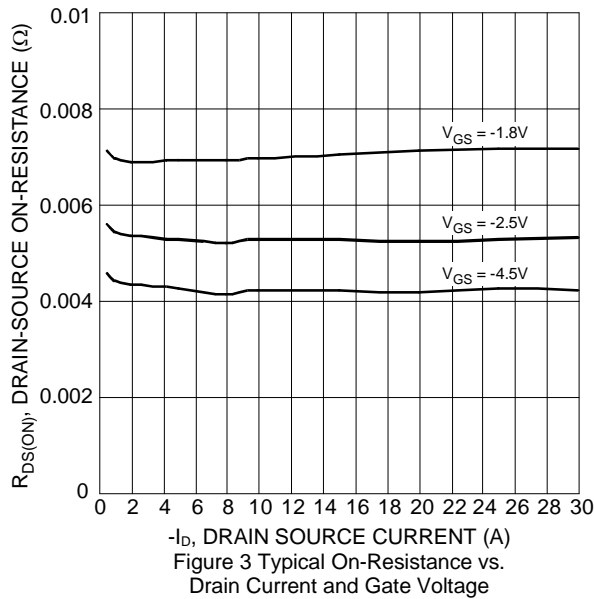
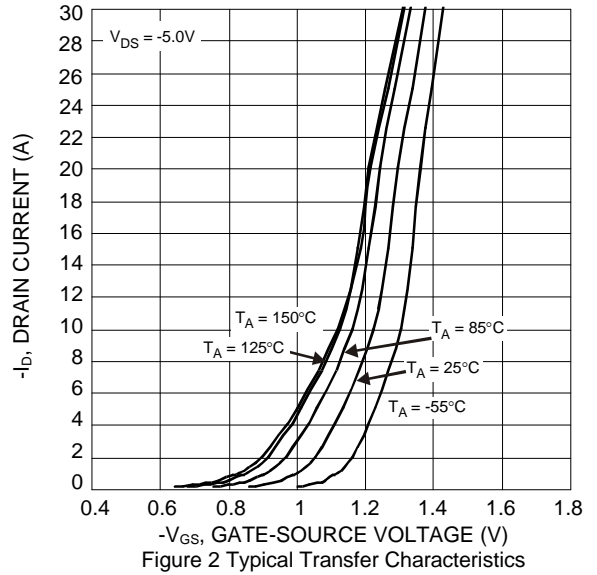
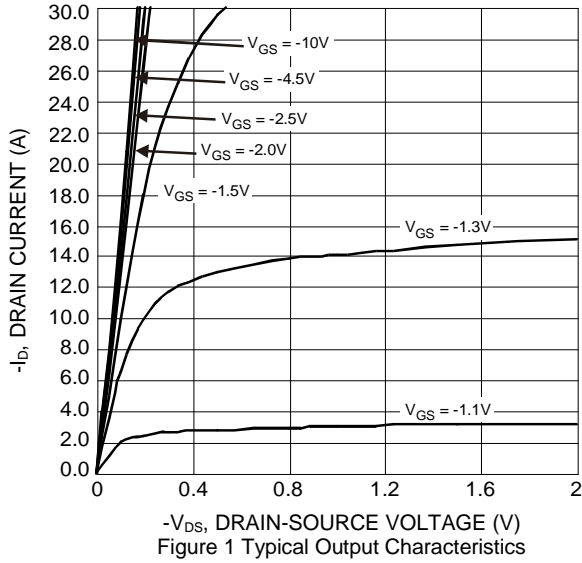
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	2.3
		T _C = +25°C	41
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 5)	54
		(Note 6)	136
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.0	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	4.2	5.5	mΩ	V _{GS} = -4.5V, I _D = -15A
		—	5.4	7.5		V _{GS} = -2.5V, I _D = -10A
		—	8	12		V _{GS} = -1.8V, I _D = -1A
		—	12	17		V _{GS} = -1.5V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -10A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{ISS}	—	5404	7500	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	728	1000		
Reverse Transfer Capacitance	C _{RSS}	—	612	900		
Gate Resistance	R _g	—	3.8	8	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	64	100	nC	V _{DD} = -10V, I _D = -20A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	140	200		
Gate-Source Charge	Q _{gs}	—	8.5	15		
Gate-Drain Charge	Q _{gd}	—	17	30		
Turn-On Delay Time	t _{D(ON)}	—	9.1	20	ns	V _{GS} = -4.5V, V _{DD} = -10V, R _g = 1Ω, I _D = -10A
Turn-On Rise Time	t _r	—	19	35		
Turn-Off Delay Time	t _{D(OFF)}	—	146	220		
Turn-Off Fall Time	t _f	—	104	150		
Reverse Recovery Time (Note 9)	t _{RR}	—	61	100	ns	I _F = -10A, di/dt = 100A/µs
Reverse Recovery Charge (Note 9)	Q _{RR}	—	44	70	nC	I _F = -10A, di/dt = 100A/µs

- Notes:
6. R_{θJA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{θJC} is guaranteed by design while R_{θJA} is determined by the user's board design.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 8. UIS in production with L = 0.1mH, T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.



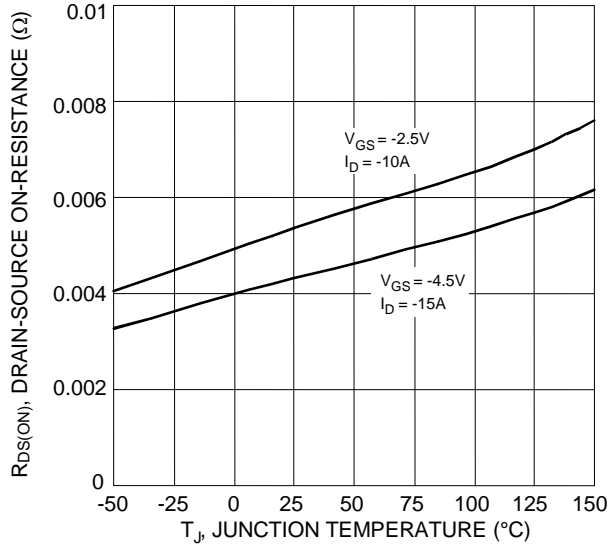


Figure 7 On-Resistance Variation with Temperature

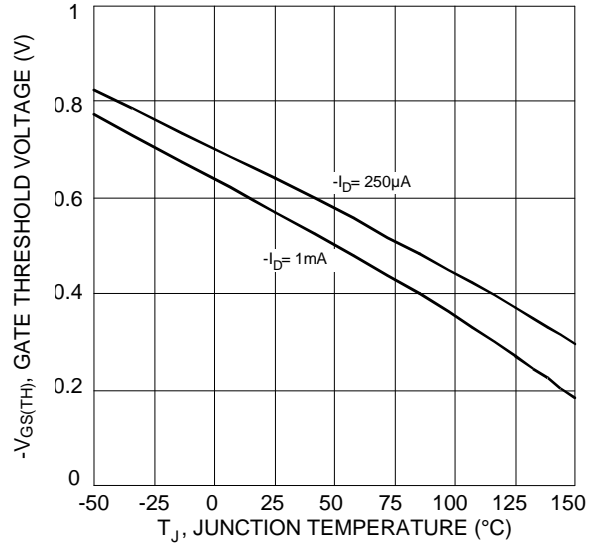


Figure 8 Gate Threshold Variation vs. Junction Temperature

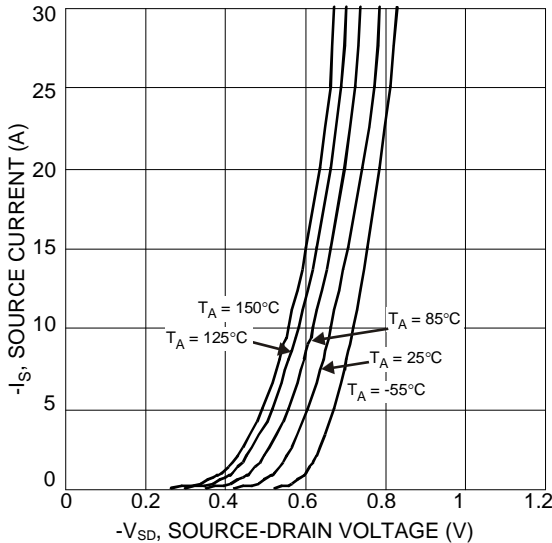


Figure 9 Diode Forward Voltage vs. Current

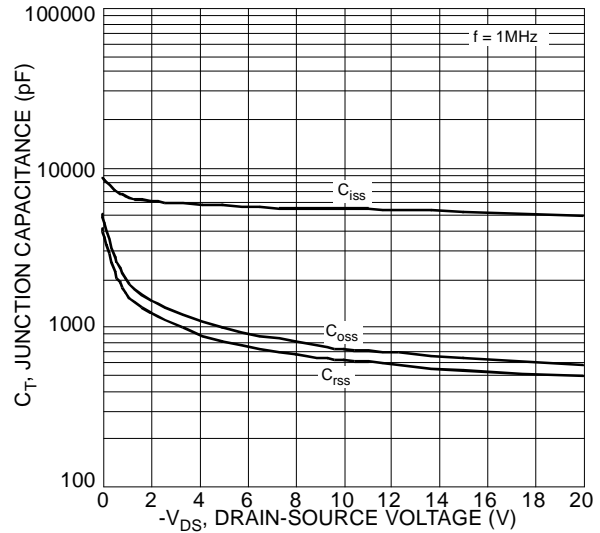


Figure 10 Typical Junction Capacitance

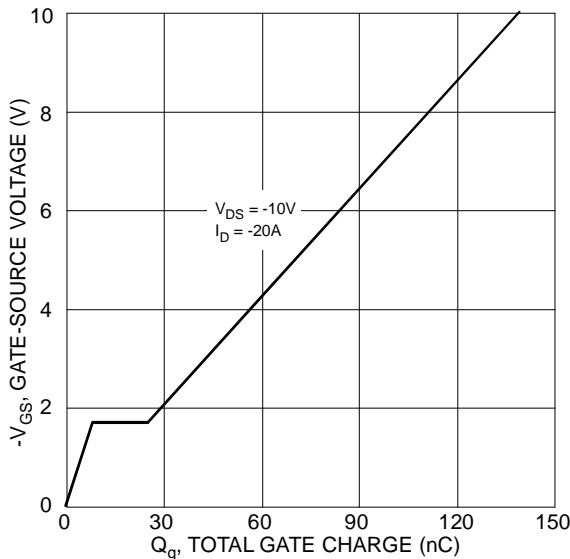


Figure 11 Gate-Charge Characteristics

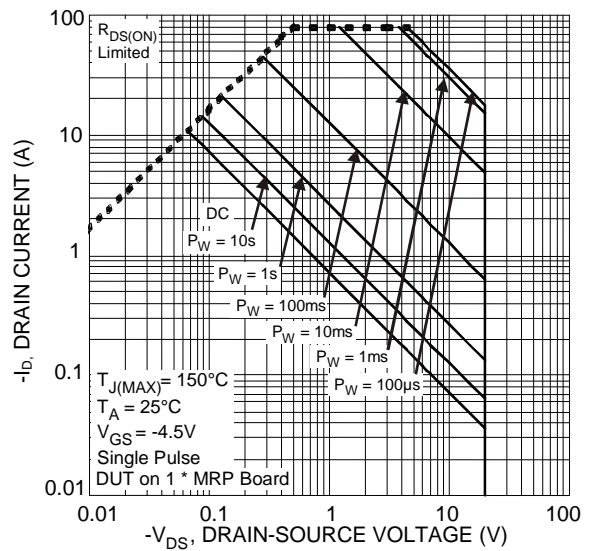
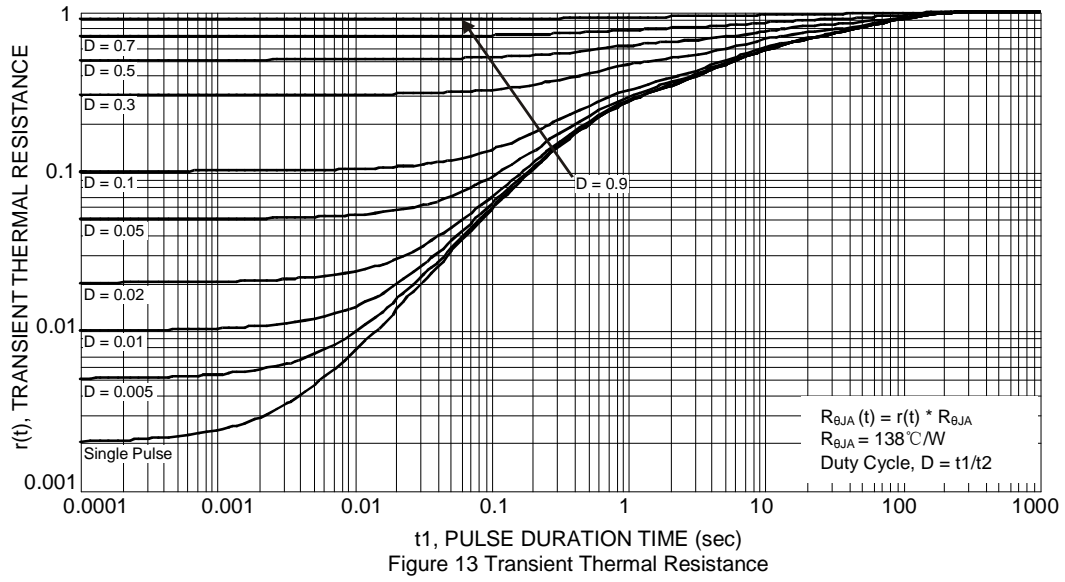


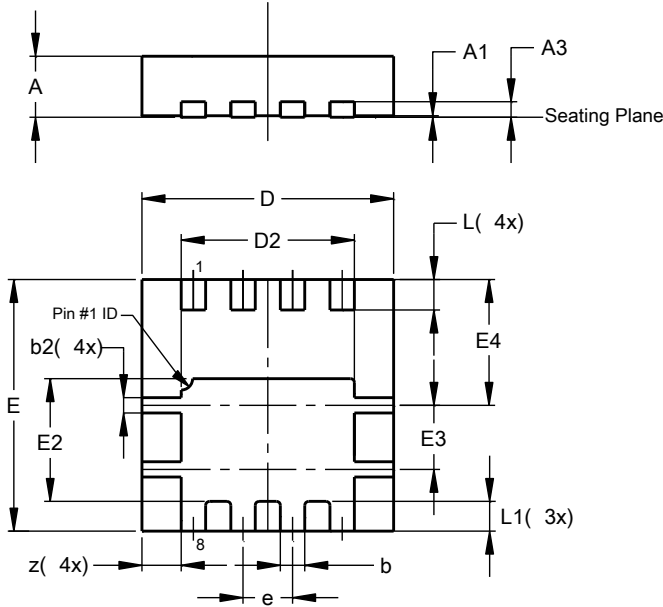
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

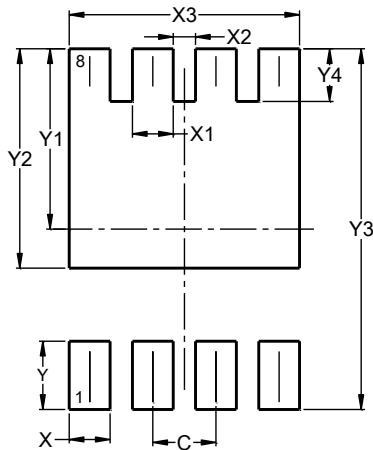


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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